

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1528	((semiconductor silicon amorphous) with (substrate wafer)) with (laser near3 anneal\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:11
L2	1528	L1 and (laser beam)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:09
L3	379	L2 and ((incident incidence reflect\$3) near4 beam)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:09
L4	285	L3 and (tilt\$2 oblique\$3 angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:09
L5	226	L4 and ((irradit\$4 irradiation irradiat\$2) with (area surface))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:09
L6	77997	(wafer substrate) with laser	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L7	41659	L6 and laser near3 beam	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L8	18096	L7 and (irradit\$4 irradiation irradiat\$2)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L9	7820	L8 and ((irradit\$4 irradiation irradiat\$2) with surface)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L10	2476	L9 and ((irradit\$4 irradiation irradiat\$2) with (target source))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12

L11	971	L10 and ((irradit\$4 irradiation irradiat\$2) with semiconductor)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L12	258	L11 and ((irradit\$4 irradiation irradiat\$2) with angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L13	64	L12 and ((tilt\$2 oblique\$3) with angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12
L14	25	L13 and (laser near3 anneal\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 15:12

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L11	0	(crystallizing near semiconductor adj film and laser adj beam and beam near3 width and thickness near3 substrate).clm.	US-PGPU B	OR	ON	2005/10/28 15:07
L12	0	(crystallizing near3 semiconductor adj film and laser adj beam and beam near3 width and thickness near3 substrate).clm.	US-PGPU B	OR	ON	2005/10/28 15:07